

Submission under 37 C.F.R. §1.114  
Serial No. 10/771,391  
Attorney Docket No. 042080

**AMENDMENTS TO THE CLAIMS**

This listing of claims replaces all prior versions of claims in the application.

1. (Currently Amended): A method of manufacturing a semiconductor device comprising, in the recited order, the steps of:

    forming an insulating film on a surface of a semiconductor element or a circuit wiring board having electrodes on the surface thereof;

    forming openings in the insulating film by patterning the insulating film and then removing portions of the insulating film above the electrodes;

    supplying a first metal into the openings;

    heating the first metal to melt and coagulate the first metal, wherein the first metal has a characteristic in which a volume thereof is increased when it is heated to be molten and coagulated in such a manner that the diameter of the opening of the insulating layer is increased;

    supplying a second metal into the openings on the coagulated first metal;

    heating the first metal and the second metal to melt and coagulate the first metal and the second metal; and

    removing the insulating film.

2. (Original): A method of manufacturing a semiconductor device according to claim 1, wherein the first metal and the second metal are supplied into the openings by an electrolytic plating method or a vapor-deposition method.

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3. (Cancelled).

4. (Previously Presented): A method of manufacturing a semiconductor device according to claim 1, wherein the first metal contains as a component thereof Bi or an alloy including Bi as a primary component.

5. (Original): A method of manufacturing a semiconductor device according to claim 4, wherein a content of Bi in the first metal is in the range from 20 to 70 wt% of the sum of the first metal and the second metal.

6. (Original): A method of manufacturing a semiconductor device according to claim 1, wherein the second metal contains as a component thereof at least one of Sn, Ag, In, Cu, Zn and Sb.

7. (Original): A method of manufacturing a semiconductor device according to claim 1, wherein the second metal is formed to such a height that it protrudes from the opening

8. (Original): A method of manufacturing a semiconductor device according to claim 1, wherein the insulating film comprises a dry film resist.

9. (Previously Presented): A method of manufacturing a semiconductor device according to claim 1, wherein the first metal and the second metal are supplied into the openings by an electrolytic plating method.